Abstracts

Fast, Accurate, On-Wafer Extraction of Parasitic Resistances and Inductances in GaAs MESFETs and HEMTs

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J.C. Costa, M. Miller, M. Golio and G. Norris. "Fast, Accurate, On-Wafer Extraction of Parasitic Resistances and Inductances in GaAs MESFETs and HEMTs." 1992 MTT-S International Microwave Symposium Digest 92.2 (1992 Vol. II [MWSYM]): 1011-1014.

A novel method of extracting the parasitic resistance and inductance values for MESFETs and HEMTs is presented. The technique requires the use of only rf two-port measurement data (ie. s-parameters), is extremely accurate, straightforward to implement and works equally well for both MESFETs and HEMTs. The technique makes use of "cold-chip" measurements in conjunction with a unique analysis that has proven to be both fast and robust.

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